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Universal Distribution of Kondo Temperatures in Dirty Metals

P. S. Cornaglia,[1] D. R. Grempel,[1] and C. A. Balseiro[2]
[1]*CEA-Saclay, DSM/DRECAM/SPCSI, Bât. 462, F-91191 Gif-sur-Yvette, France*
[2]*Centro Atómico Bariloche, 8400 San Carlos de Bariloche, Río Negro, Argentina*

Kondo screening of diluted magnetic impurities in a disordered host is studied analytically and numerically in one, two and three dimensions. It is shown that in the $T_{\rm K}\to 0$ limit the distribution of Kondo temperatures has a universal form, $P(T_{\rm K})\sim T_{\rm K}^{-\alpha}$ that holds in the insulating phase and persists in the metallic phase close to the metal insulator transition. Moreover, the exponent α depends only on the dimensionality. The most important consequence of this result is that the T dependence of thermodynamic properties is smooth across the metal-insulator transition in three dimensional systems.

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In a class of compounds with coexisting magnetic moments and conduction electrons the magnetic susceptibility and the specific heat coefficient exhibit anomalous power law or logarithmic low temperature divergences. However, magnetic order is not observed down to the lowest attainable temperatures [1]. This behavior is observed in a growing family of heavy-fermion compounds [2] an also in the doped semiconductor Si:P [3].

It was early recognized that this type of non-Fermi liquid (NFL) anomaly is associated with the interplay of the Kondo effect and strong disorder. In heavy fermions disorder is present mostly in the f-electron sub-system. In a clean system screening of f-moments starts at the single-impurity Kondo scale $T_{\rm K}\sim\exp[-1/(J\rho_0)]$ where J is the Kondo coupling and ρ_0 is conduction electron density of states (DOS) at the Fermi level. In the dirty case J is a random variable with a distribution $P(J)$. Therefore, the local values of $T_{\rm K}$ are also random and have a distribution $P(T_{\rm K})$ solely determined by $P(J)$. The simple Kondo-disorder model [4] and its subsequent improvements [5], based on the above physical picture, lead quite naturally to NFL phenomenology.

One might think that when the disorder is mostly present in the *conduction band* $P(T_{\rm K})$ is similarly determined by $\rho(\mathbf{R},\varepsilon_{\rm F})$, the distribution of the local DOS (LDOS) of the host at the Fermi level at the position of the Kondo impurity [6].

In this Letter we show that this is not the case except at weak disorder. In general, $P(T_{\rm K})$ depends on subtle features of the LDOS and its statistical properties, not simply on the distribution of its values at the Fermi energy [7, 8, 9]. The most important consequence of the analysis presented below is that in the limit $T_{\rm K}\to 0$, the form of $P(T_{\rm K})$ is *universal* in the insulating phase. We find that $P(T_{\rm K})\sim A\,T_{\rm K}^{-\alpha}$ where A is a non-universal amplitude and the exponent α depends only on the dimensionality. Furthermore, the same behavior is obtained for the metallic phase close to the metal insulator transition, with an identical exponent.

We discuss the problem of a single magnetic impurity Kondo-coupled to a disordered bath of non-interacting electrons. We represent the host by an Anderson model with random site energies uniformly distributed in an interval $[-W/2,W/2]$. Without loss of generality we shall set the chemical potential to zero and place the impurity at $\mathbf{R}$=0. We shall denote the dimensionality of the system by D (D = 1, 2 and 3). The host is an insulator for $W>W_c$ where W_c is finite in three dimensions (3D) and $W_c=0$ in one (1D) and two dimensions (2D).

Following previous authors [5, 6] we use slave-boson mean field theory to write down an implicit equation for $T_{\rm K}$

$$\frac{2}{J} = \int_{-\infty}^{\infty}\frac{d\varepsilon}{\varepsilon}\,\tanh(\varepsilon/2T_{\rm K})\,\rho(\varepsilon,\mathbf{0})\,. \qquad (1)$$

Here, $\rho(\varepsilon,\mathbf{0})=\sum_\ell\delta(\varepsilon-\varepsilon_\ell)\,|\psi_\ell(\mathbf{0})|^2$ is the LDOS of the host at $\mathbf{R}=0$, where $\psi_\ell(\mathbf{R})$ is the ℓ-th eigenfunction of the host and ε_ℓ is its associated eigenvalue for a fixed realization of the disorder. This formula is identical to what is obtained defining $T_{\rm K}$ as the temperature at which second order perturbation in J breaks down [10].

In the first part of the Letter we discuss extensively the properties of $P(T_{\rm K})$ in the Anderson insulator for which a number of results can be obtained using physical arguments and the solving analytically a simplified model that captures the essential physics. Then, we present the results of numerical simulations for all the insulating phases and for the metallic phase in 3D.

In an Anderson insulator the wave functions are localized around random positions $\mathbf{R}_\ell$. At long distances from their peak positions they decay as $|\psi_\ell(\mathbf{R}-\mathbf{R}_\ell)|^2\sim\exp(-2|\mathbf{R}-\mathbf{R}_\ell|/\xi_\ell)$ where $\xi_\ell\equiv\xi(\varepsilon_\ell)$ is the energy-dependent localization length. Since $\xi(\varepsilon)$ is smooth on the scale of $T_{\rm K}$ we shall neglect its energy dependence and denote its value at $\varepsilon=0$ by ξ. The eigenvalues ε_ℓ are random variables and their distribution is Poissonian [11].

For a fixed configuration of the site energies the LDOS consists of a dense set of δ-functions with varying amplitudes. There are $\mathcal{O}(\xi^D)$ peaks with weights $\mathcal{O}(\xi^{-D})$ that come from states localized within a volume of size ξ^D around the impurity and infinitely many small peaks with exponentially smaller weights that come from states localized outside this volume. The mean separation between the main peaks is $\Delta E_\xi \sim B(W)/\xi^D$ where $B(W)$ is the bandwidth (*i.e.* the support of the LDOS).

Consider first the contribution of the largest peaks to the LDOS and neglect the rest. The conditions of validity of this approximation will be discussed below. It is convenient to split the interval of integration in Eq. (1) in subintervals of width $T_{\rm K} << B(W)$. Within each of these the function $\tanh(\varepsilon/2T_{\rm K})/\varepsilon$ is essentially constant and can be safely taken out of the sub-integral. Then, the LDOS in Eq. (1) can be well approximated by the coarsegrained function $\rho_s(\varepsilon) \sim N_p(\varepsilon, T_{\rm K})/(\xi^D T_{\rm K})$ where $N_p(\varepsilon, T_{\rm K})$ is the number of large peaks with energies in an interval of width $T_{\rm K}$ around ε. It is clear that $\overline{N_p(\varepsilon, T_{\rm K})} = \xi^D T_{\rm K}/B(W)$ and $\overline{\rho}_s = B^{-1}(W)$. The LDOS may be split in two parts, $\rho_s(\varepsilon) = \overline{\rho}_s + \delta\rho_s(\varepsilon)$ where $\delta\rho_s(\varepsilon)$ is a random function with zero mean.

Suppose that $\overline{N_p} \gg 1$. Then, $\delta\rho_s(\varepsilon)$ is a Gaussian random function with $\overline{\delta\rho_s(\varepsilon)\ \delta\rho_s(\varepsilon')} = \overline{\rho}_s\ \xi^{-D}\ \delta(\varepsilon - \varepsilon')$. Equation (1) and elementary properties of Gaussian random functions lead readily to

$$P(T_{\rm K}) \propto \exp\left[-\frac{\ln^2\left(T_{\rm K}/T_{\rm K}^0\right)}{2(\xi_{\rm K}/\xi)^D}\right]. \qquad (2)$$

This is a log-normal distribution centered at $T_{\rm K}^0$, the Kondo temperature of a clean system with a uniform LDOS $\overline{\rho}_s$. The variance of the distribution is $\sigma^2 = (\xi_{\rm K}/\xi)^D$ where $\xi_{\rm K}^D = 1/(T_{\rm K}^0\rho_0)$ is the volume of the Kondo screening cloud [12]. Since $\sigma^{-2} \sim \overline{N_p}$, Eq. (2) is valid for $\xi \gtrsim \xi_{\rm K}$. In this regime most of the impurities have Kondo temperatures in a narrow interval around $T_{\rm K}^0$ and yet we are in an insulating state.

This is not the end of the story. Even for $\xi > \xi_{\rm K}$ the condition $\overline{N_p} \gg 1$ is violated for $T_{\rm K} \lesssim B(W)/\ \xi^D$. For these temperatures, the number of large peaks with energies in an interval $T_{\rm K}$ around the Fermi energy is small. They no longer dominate the LDOS as assumed and screening of the impurity must be done by electron states localized far away from the former. But these are precisely those that we neglected from the start. We then expect that for $\xi > \xi_{\rm K}$ $P(T_{\rm K})$ will show, in addition of the peak around $T_{\rm K}^0$, a low temperature tail appearing below $T_{\rm K}\ \sim B(W)/\ \xi^D$ carrying a small fraction of the weight of the former. For $\xi < \xi_{\rm K}$ there is no temperature range in which Eq. (2) holds and we do not expect to find a sharp peak near $T_{\rm K}^0$. The tail should still appear below $\sim T_{\rm K}^0$.

In order to gain insights on the properties of the low-temperature tail in $P(T_{\rm K})$ we now discuss an exactly solvable "toy" model for the insulating phase that reveals interesting features that we shall retrieve in the numerical solution of the Anderson model presented below.

As stated above the localized functions $\psi_\ell(\mathbf{R})$ decay exponentially away from their peak positions. However, they fluctuate randomly around the envelope $\sim \exp(-R/\xi)$. In our toy model these fluctuations are ignored and the true eigenfunctions are replaced by normalized exponentials centered around their random locations. Furthermore, these positions $\mathbf{R}_\ell$ are assumed to be uncorrelated with the energies. This holds deep in the insulating phase. Equation (1) becomes

$$\frac{2}{J} = \sum_\ell \frac{e^{-2R_\ell/\xi}}{\mathcal{N}_D}\frac{\tanh(\varepsilon_\ell/2T)}{\varepsilon_\ell} \equiv F_T(\{\varepsilon_\ell\})\ , \qquad (3)$$

where the normalization $\mathcal{N}_D = 2^{-D}\Omega_D\xi^D(D-1)!$, Ω_D is the solid angle in D dimensions and the last term in the above equation defines the random function F_T.

A key feature of Eq. (3) is that F_T is a monotonically decreasing function of T. A moment's reflection will convince the reader that this implies

$$P(F_T < 2/J) = P(T_{\rm K} < T) + P(T_{\rm K} = 0)\ , \qquad (4)$$

where the first term on the right hand side is the integrated probability of $T_{\rm K}$ from zero to T, and the second is the probability of the impurity remaining unscreened at $T = 0$. Therefore, the distribution of *non-zero* Kondo temperatures is given by

$$P(T_{\rm K}) = \int_0^{2/J} \left.\frac{\partial W_T(x)}{\partial T}\right|_{T=T_{\rm K}} dx, \qquad (5)$$

where $W_T(x) = \overline{\delta\left(F_T\left(\{\varepsilon_\ell\}\right) - x\right)}$ is the probability density of F_T. In our toy model $W_T(x)$ can be calculated analytically leading to a closed form expression for $P(T_{\rm K})$.

Here, we are interested in the asymptotic properties in three relevant regimes. For $T_{\rm K}/W \gg 1/\mathcal{N}_{\mathcal{D}} \sim \xi^{-D}$ we find that $P(T_{\rm K})$ sharply decays for large $T_{\rm K}$ as $\sim \exp(-C\xi^D T_{\rm K}\ln^2 T_{\rm K})$ where C is a constant of order one. The same expansion is valid for $\xi > \xi_{\rm K}$, $T_{\rm K} \sim T_{\rm K}^0$ and in this case we retrieve precisely Eq. (2).

More importantly, we can now have access to the low-temperature region that was beyond the scope of the qualitative analysis presented above. In the limit $T \to 0$ we find

$$P(T_{\rm K}) \sim \Omega_D\left(\frac{\xi}{2}\right)^D |\log(T_{\rm K}/W)|^\alpha \quad \text{for } T_{\rm K} \to 0\ , \qquad (6)$$

with $\alpha = D - 1$. The asymptotic form of $P(T_{\rm K})$ for this model is thus a power of the logarithm with an exponent depending only on dimensionality. The prefactor, proportional to ξ^D, decreases with increasing disorder. A more detailed analysis shows that this divergent contribution appears at very low temperatures for $\xi \gg \xi_{\rm K}$. With increasing disorder the tail shifts to higher temperatures.

The model discussed above is based on a crude representation of the localized states. Furthermore, it can obviously not describe the metallic phase in 3D or the metal-insulator transition (MIT). Therefore, we turn to our numerical results for the Anderson model (AM). It will be seen that the two models share the same *qualitative* properties. Namely, a divergent $P(T_{\rm K})$ at low $T_{\rm K}$ with the nature of the divergence depending only the spatial dimension and not on disorder. We shall also see that $P(T_{\rm K})$ acquires the *same* form in the localized and metallic phases in 3D.

Our numerical calculations were performed using a representation of the host by the Anderson model on a regular lattice of size L^D for $D = 1$, 2, and 3:

$$H_A = \sum_{i,\sigma} \varepsilon_i c^\dagger_{i\sigma} c_{i\sigma} - t \sum_{\langle i,j \rangle,\sigma} c^\dagger_{i\sigma} c_{j\sigma} \; , \tag{7}$$

where ε_i are random variables and the hopping integral between nearest neighbors $t = 1$ is the unit of energy. We show results for $J = 1/4B$, where B is the bandwidth of the clean system, and for ε_i uniformly distributed in the interval $[-W/2, W/2]$. We have checked the robustness of our results, in particular the value of the exponent of the power law, analyzing other values of J and considering a Gaussian distribution for ε_i.

For each lattice size and each realization of the random potential the Anderson Hamiltonian was diagonalized and Eq. (1) was solved for $T_{\rm K}$ using the numerical eigenfunctions and eigenvalues. Histograms were constructed repeating the procedure for many realizations of the potential and positions of the impurity. The size of the lattice and the number of realizations was increased until convergence of the histograms. The values of the parameters appear in the captions of the figures.

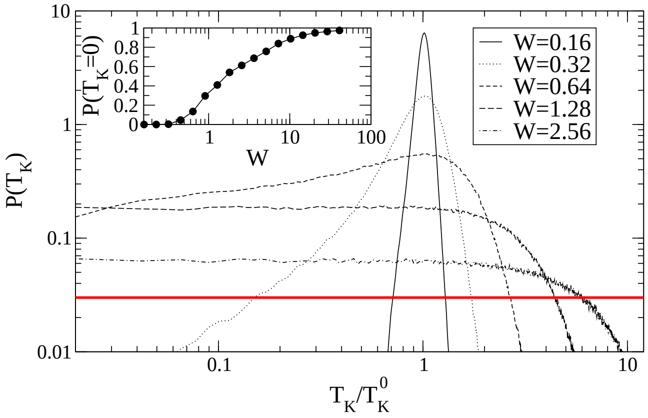

FIG. 1: $P(T_{\rm K})$ in 1D for several values of the amplitude of the disorder. Results for a chain of $N_s = 1000$ sites. The number of realizations of the potential is 1000. Inset: Fraction of unscreened impurities at $T = 0$ as a function of disorder.

Figure 1 displays the distribution of Kondo temperatures in $D = 1$. It is seen that at small disorder $P(T_{\rm K})$ is strongly peaked at $T^0_{\rm K}$. For $W \ll 1$ the shape of the peak fits accurately Eq. (2). With increasing disorder $P(T_{\rm K})$ first broadens and departs from the log-normal distribution, and a tail appears at low temperatures. Upon increasing further the disorder, the peak at $T_{\rm K} = T^0_{\rm K}$ disappears and $P(T_{\rm K})$ becomes flat as in the toy model.

The fraction of unscreened impurities at $T = 0$ as a function of disorder is shown in the inset to Fig. 1. $P(T_{\rm K} = 0)$ increases continuously with disorder from vanishingly small values for $W \sim 0$ to $\mathcal{O}(1)$ for large W. We independently estimated ξ as a function of disorder and checked that the crossover between the two regimes takes place when $\xi \sim \xi_{\rm K}$, as expected from our qualitative arguments.

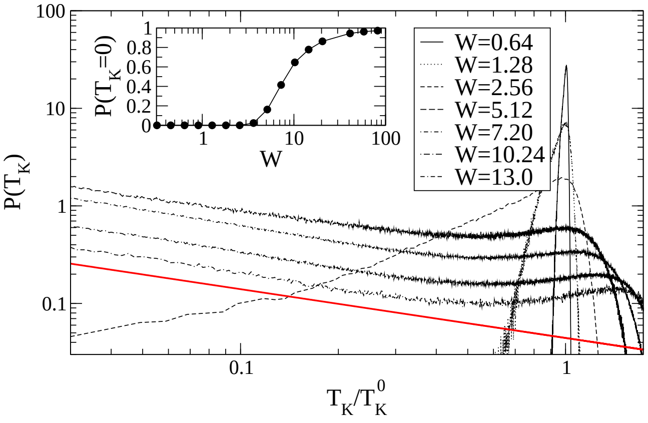

FIG. 2: $P(T_{\rm K})$ in 2D for several values of the amplitude of the disorder. Results for square lattices of $N_s = 2025$ sites and 1000 realizations of the amplitude of the potential. The slope of the thick straight line is -0.5. Inset: Fraction of unscreened impurities at $T = 0$ as a function of disorder.

The results for the two dimensional case are displayed in Fig. 2. The same general trends are also observed in this case but in two dimensions $P(T_{\rm K})$ is no longer flat but divergent at low $T_{\rm K}$ as expected from our analytical results. Note that the straight lines corresponding to different values of W are parallel meaning that $P(T_{\rm K})$ is a power law with a *disorder independent* exponent. The thick straight line has slope $-1/2$ suggesting that $\alpha = 1/2$ in 2D.

For temperatures below the range plotted in the figure finite-size effects come into play. These are expected for $T_{\rm K} \lesssim \Delta$, the typical level spacing at the Fermi level $\propto L^{-D}$ [13]. We have thus performed a careful study of these effects and checked that the power law behavior extends to lower and lower values of $T_{\rm K}$ as the size of the system increases.

The results for the 3D case, displayed in Fig. 3, are the most interesting ones because in this case there is a MIT at $W_c \sim 16.5$ [14]. As in the 2D case, $P(T_{\rm K})$ is a power law at low temperature but the slope of the thick straight line is now $-3/4$ suggesting that this is the value of the exponent in 3D. A striking new feature in 3D is that the form of $P(T_{\rm K})$ and the exponent are *the same* on both sides of the MIT. This can be seen by comparing the two lowermost curves in Fig. 3, that correspond to $W > W_c$, to the two above them that correspond to $W < W_c$. The total contribution of the impurities to the susceptibility or specific heat can be calculated using interpolation formulas (see e.g. Ref. [16]) and weighting the individual contributions with P(T_K). An important consequence is that the magnetic susceptibility and the specific heat coefficient in this model should exhibit a power law behavior with a disorder independent exponent, $\chi \sim \gamma \sim T^{-\alpha}$, and be

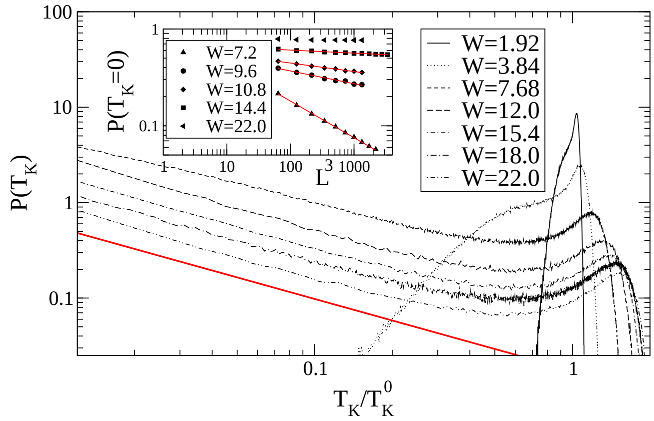

FIG. 3: $P(T_{\rm K})$ in 3D for several values of the amplitude of the disorder. Results for cubic lattices of $N_s = 2197$ sites and 1000 realizations of the amplitude of the potential. The MIT occurs at $W_c \sim 16.5$. The slope of the thick straight line is -0.75. Inset: size and disorder dependence of $P(T_{\rm K} = 0)$ in the metallic phase.

continuous across the MIT. Interestingly, this is precisely what was observed in Si:P which has a MIT as a function of the concentration of P and shows signatures of local magnetic moments in both the metallic and insulating phases [3, 17]. Although the agreement obtained is very appealing, this system contains physical ingredients which are out of the scope of our model.

We found that in our finite systems a fraction of the spins remains unscreened down to zero temperature. This fraction, very small for small disorder, increases as $W \to W_c$. Since on general grounds, in the thermodynamic limit, all spins must be screened at $T = 0$ in the metallic phase, the observed effect is due to finite-size. The inset to Fig. 3 displays the results of a finite-size scaling analysis of $P(T_{\rm K} = 0)$ for several values of W. It can be seen that $P(T_{\rm K} = 0)$ scales to zero in the metallic phase with increasing L as it should. Moreover, $P(T_{\rm K} = 0) \propto L^{-\beta(W)}$ with an exponent $\beta(W)$ that depends on the disorder and that decreases as W increases. In contrast, deep in the insulating phase, $P(T_{\rm K} = 0)$ remains finite in the thermodynamic limit [7].

In this Letter we have studied the single-impurity problem and our results are strictly applicable in the diluted limit. We showed that the structure of the LDOS induces a power law $P(T_{\rm K})$ in the insulating phase. This low $T_{\rm K}$ divergence is associated to impurities screened by states localized at distances larger the localization length ξ. The statistical properties of these *far* states are such that a change in the disorder strength shifts the onset temperature of the diverging behavior but not the nature of the divergence. Surprisingly, the exponent of the power law is disorder independent and in 3D the same behavior persists across the MIT with an identical exponent.

In concentrated systems interaction effects can not be ignored. An extension of the Dynamical Mean Field Theory (DMFT) method for random systems was used with success in that context [8, 15]. A power law $P(T_{\rm K})$ was found for the disordered Anderson model on a Bethe lattice using DMFT in Ref. [16]. An important difference between this work and ours is that the exponent of the power law found in Ref. [16] depends on the strength of disorder and is therefore non-universal. It would be very interesting to investigate how our results for the diluted case evolve with increasing density and what is the role of the lattice geometry.

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After the completion of this work we became aware of a related study by S. Kettemann and E. R. Mucciolo [18].

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